AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows.

1.- 59. (Canceled)

60. (Previously presented) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate by using a CVD system;

forming a semiconductor film comprising amorphous silicon on said silicon nitride film;

forming a silicon oxide film on said semiconductor film;

disposing a solution in contact with said silicon oxide film, said solution containing a metal being capable of promoting crystallization of said semiconductor film;

heating said semiconductor film and said metal to crystallize said semiconductor film; and

irradiating laser beam to said semiconductor film to improve the crystallinity thereof.

61. (Previously presented) A method according to claim 60 wherein said CVD system is selected from a plasma CVD system and an LPCVD system.

62. (Previously presented) A method according to claim 60 wherein said metal is selected from the group consisting of nickel, palladium, platinum, copper, silver, gold, indium, tin, phosphorous, arsenic and antimony.

63. – 71. (Canceled)

72. (Previously presented) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate by using a CVD system;

forming a semiconductor film comprising amorphous silicon on said silicon nitride film;

forming a silicon oxide film on said semiconductor film;

disposing a solution comprising a metal compound in contact with said silicon oxide film;

heating said semiconductor film to crystallize said semiconductor film; and

irradiating laser beam to said semiconductor film to improve the crystallinity thereof.

73. (Previously presented) A method according to claim 72 wherein said CVD system is selected from a plasma CVD system and an LPCVD system.

74. (Previously presented) A method according to claim 72 wherein said metal compound is selected
from the group consisting of nickel bromide, nickel acetate, nickel oxalate, nickel carbonate, nickel chloride, nickel iodide, nickel nitrate, nickel sulfate, nickel formate, nickel acetylacetonate, nickel 4-cyclohexybutyrate, and nickel hydroxide.

75. – 80. (Canceled)

81. A method according to claim 60 wherein said silicon nitride film is in contact with said semiconductor film.

82. (Canceled)

83. (Previously presented) A method according to claim 72 wherein said silicon nitride film is in contact with said semiconductor film.

84. (Previously presented) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;

forming a semiconductor film comprising amorphous silicon on said silicon nitride film;

forming a silicon oxide film on said semiconductor film;

disposing a solution in contact with said silicon oxide film, said solution containing a metal being capable of promoting crystallization of said semiconductor film; and

heating said semiconductor film and said metal to crystallize said semiconductor film.

85. (Previously presented) A method according to claim 84 wherein said metal is selected from the group consisting of nickel, palladium, platinum, copper, silver, gold, indium, tin, phosphorous, arsenic and antimony.

86. (Previously presented) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;

forming a semiconductor film comprising amorphous silicon on said silicon nitride film;

forming a silicon oxide film on said semiconductor film;

disposing a solution comprising a metal compound in contact with said silicon oxide film; and

heating said semiconductor film to crystallize said semiconductor film.

87. (Previously presented) A method according to claim 86 wherein said metal compound is selected from the group consisting of nickel bromide, nickel acetate, nickel oxalate, nickel carbonate, nickel chloride, nickel iodide, nickel nitrate, nickel sulfate, nickel formate, nickel acetylacetonate, nickel 4-cyclohexybutyrate, and nickel hydroxide.

88. (Previously presented) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;

forming a semiconductor film comprising amorphous silicon on said silicon nitride film;

forming a silicon oxide film on said semiconductor film;

disposing a solution in contact with said silicon oxide film, said solution containing a metal being capable of promoting crystallization of said semiconductor film;

heating said semiconductor film and said metal to crystallize said semiconductor film; and

irradiating laser beam to said semiconductor film to improve the crystallinity thereof.

89. (Previously presented) A method according to claim 88 wherein said metal is selected from the group consisting of nickel, palladium, platinum, copper, silver, gold, indium, tin, phosphorous, arsenic and antimony.

90. (Previously presented) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;

forming a semiconductor film comprising amorphous silicon on said silicon nitride film;

forming a silicon oxide film on said semiconductor film;

disposing a solution comprising a metal compound in contact with said silicon oxide film;

heating said semiconductor film to crystallize said semiconductor film; and

irradiating laser beam to said semiconductor film to improve the crystallinity thereof.

91. (Previously presented) A method according to claim 90 wherein said metal compound is selected from the group consisting of nickel bromide, nickel acetate, nickel oxalate, nickel carbonate, nickel chloride, nickel iodide, nickel nitrate, nickel sulfate, nickel formate, nickel acetylacetonate, nickel 4-cyclohexybutyrate, and nickel hydroxide.

92. (New) A method according to claim 60 wherein said semiconductor film does not orient along a crystallographic (111) plane.

93. (New) A method according to claim 72 wherein said semiconductor film does not orient along a crystallographic (111) plane.

94. (New) A method according to claim 84 wherein said semiconductor film does not orient along a crystallographic (111) plane.

95. (New) A method according to claim 86 wherein said semiconductor film does not orient along a crystallographic (111) plane.

96. (New) A method according to claim 88 wherein said semiconductor film does not orient along a crystallographic (111) plane.

97. (New) A method according to claim 90 wherein said semiconductor film does not orient along a crystallographic (111) plane.